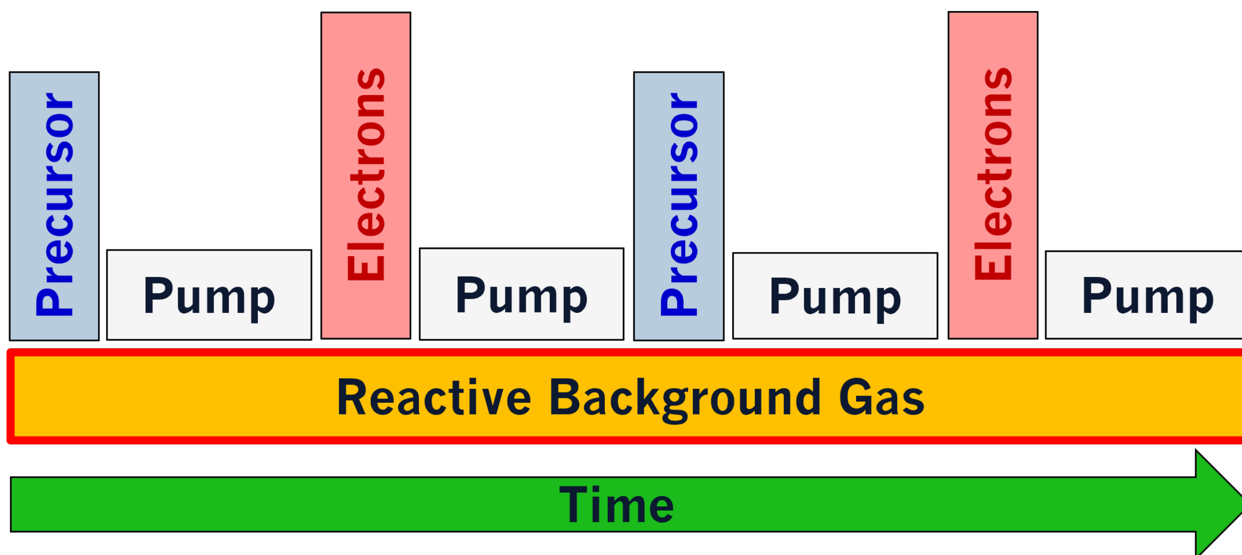

Figure 1. Schematic of EE-ALD performed with continuous reactive background gas. Sequential precursor and electron exposures define EE-ALD. The continuous reactive background gas present during EE-ALD can tune the EE-ALD film composition.

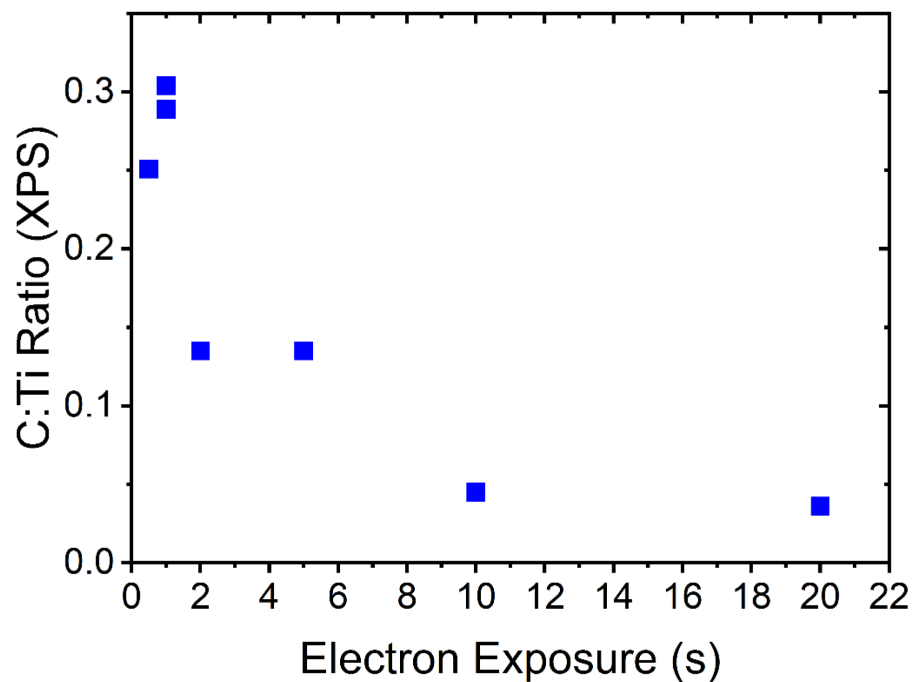

Figure 2. Plot of the C:Ti ratio for several TiCN films as a function of the electron exposure time. Longer electron exposures led to lower C incorporation into the films.